N-Channel 80-V (D-S) MOSFET

Key Features:

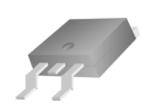
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

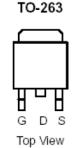
Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)}(m\Omega)$				
80	$4.5 @ V_{GS} = 10V$	90 ^a			
60	$6 @ V_{GS} = 4.5V$	90			







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			80	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current a	T _C =25°C	I_D	90	Α		
Pulsed Drain Current ^b		I _{DM}	390	ζ		
Continuous Source Current (Diode Conduction) ^a	I _S	110	Α			
Power Dissipation ^a	T _C =25°C	P_{D}	300	W		
Operating Junction and Storage Temperature Range		T_J , T_{stg}	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Ambient ^a	$R_{\theta JA}$	62.5	°C/W			
Maximum Junction-to-Case	$R_{\theta JC}$	1	C/VV			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

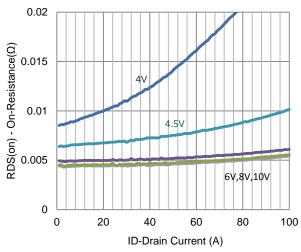
Electrical Characteristics

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit		
Static								
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA		
Zero Gate Voltage Drain Current	lana	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$	V		1	uA		
Zero Gate Voltage Brain Gurrent	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$	25			uA		
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	120			Α		
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$			4.5	mΩ		
Diain-Source On-Resistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			6	11122		
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 20 \text{ A}$		30		S		
Diode Forward Voltage	V_{SD}	$I_{S} = 55 \text{ A}, V_{GS} = 0 \text{ V}$		0.84		V		
		Dynamic						
Total Gate Charge	Q_g	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V},$		113		nC		
Gate-Source Charge	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 20 \text{ A}$		24				
Gate-Drain Charge	Q_gd	10 - 20 A		67				
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 40 \text{ V}, R_{L} = 2 \Omega,$		42				
Rise Time	t _r	$V_{DS} = 40 \text{ V}, N_L - 2 \Omega,$ $I_D = 20 \text{ A},$		90		ns		
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		325				
Fall Time	t _f	VGEN = 10 V, NGEN = 0 12		117				
Input Capacitance	C _{iss}			9924				
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		959		pF		
Reverse Transfer Capacitance	C_{rss}			852				

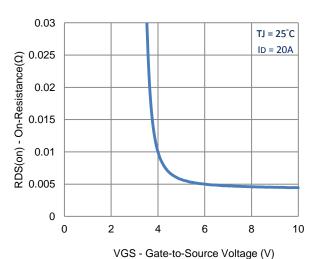
Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

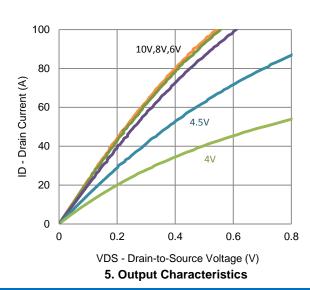
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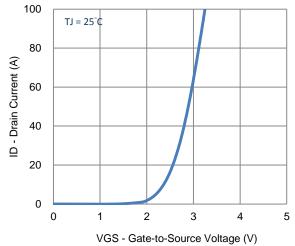
1. On-Resistance vs. Drain Current



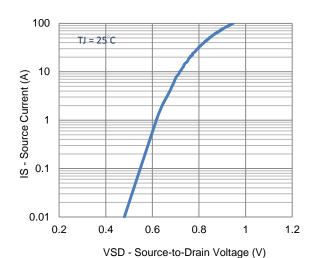
3. On-Resistance vs. Gate-to-Source Voltage



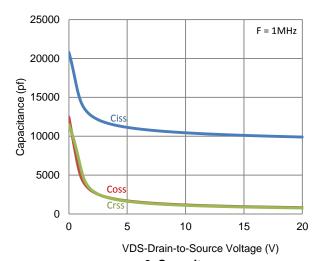
Typical Electrical Characteristics



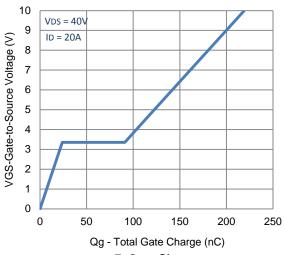
2. Transfer Characteristics

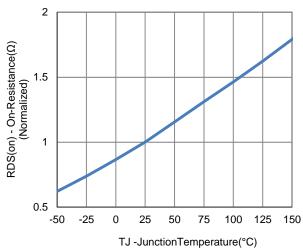


4. Drain-to-Source Forward Voltage



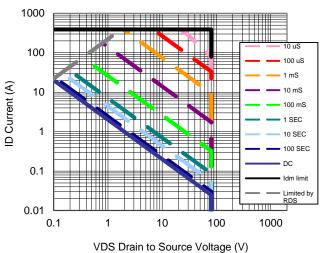
Typical Electrical Characteristics

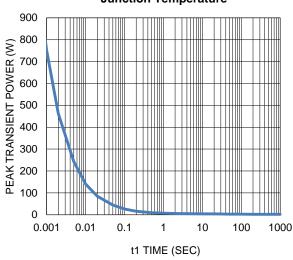




7. Gate Charge

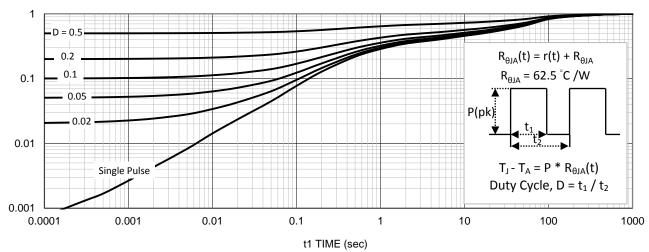






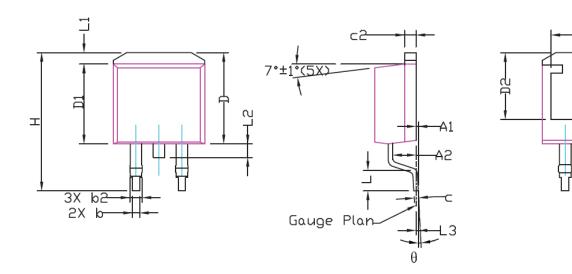
9. Safe Operating Area

10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



CVADEI	DIMENS:	IONAL F	REQMTS	INCH	ES REG	2TM	
SYMBOL	MIN	NDM	MAX	MIN	NDM	MAX	
Α	4,30	4.57	4,72	0.169	0.180	0.186	
A1	0		0,25	0		0.010	
A2	2,47	2.57	2,67	0.097	0.101	0.105	
b	0.69	0,813	0.94	0.027	0.032	0.037	
b2	1.17	1.27	1,45	0.046	0.050	0.057	
С	0.48	0,50	0.60	0.019	0.020	0.024	
c2	1,17	1.27	1,37	0.046	0.050	0.054	
D	9,80	10.05	10,30	0.386	0,396	0.406	
D1	8,64	8.78	9,65	0.340	0.346	0.380	
D2	7.12	7,37	7,62	0.280	0,290	0.300	
E	9,70	10.15	10.54	0,382	0,400	0.415	
E1	8,00	8,20	8,40	0.315	0,323	0.331	
е	2.54 BSC			0.3	0.100 BSC		
H	14,99	15.24	15,49	0.590	0.600	0.610	
L	1,78	2.29	2.79	0.070	0.090	0.110	
L1	1.02	1.27	1.52	0.040	0.050	0,060	
L2			1.75			0.069	
L3		0,254			0.010		
θ	0.		8*	0°		8*	

e 2X